U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

SERIAL NO. Filed Herewith ATTY. DOCKET NO. MI22-1741

LIST OF ART CITED BY APPLICANT

Form PTO-1449

(Use several sheets if necessary)

APPLICANT Klaus Florian Schuegraf et al. FILING DATE GROUP

SIS

							Filed Herewith		Unkno		00	
					U.S. PA	TENT DOCUMENTS					Ja	
*Examiner		Docu Numi		Date		Name		Class	Subclass	Filing If Appro		
EO	AA	5,425	,392	06/95	Thakur et a	al.						
e.	AB											
	AC	<i>-</i> .										
	AD						·			-		
gar ta ila	AE .		***								:	
1.13 No. 4	AF											
	. AG		•									
au an an a	АН	::::::::::::::::::::::::::::::::::::										
	ΑĬ		•								•	
	AJ	,								:		
	AK								!			
					FOREIGN	PATENT DOCUMEN	rts					
		Document Number		Date	Country			Class	Subclass	Translation		
	AL					<u> </u>	•		·	Yes	No	
	AL.	<u> </u>	ОТІ	HER REFERE	NCES (includin	ng Author, Title, Dat	e, Pertinent Pages, Etc	:.)				
* 10 1 1 ******************************	. AK	. G	Taishi Kubota et:al.; "The Effect of the Floating Gate/Tunnel SiO ₂ Interface on FLASH Memory Data Retention Reliability"; 1994; 2 pages									
EO		rei.u										
A .u	AL	O -	Shoue Jen Wang et al.; "Effects of Poly Depletion on the Estimate of Thin Dielectric Lifetime"; IEEE Electron Device Letters, Vol. 12, No. 11,									
EO			November 1991; pp. 617-619									
T= 1071	AM t	· z · 3	Klaus F. Schuegraf et al.; "Impact of Polysilicon Depletion in Thin Oxide MOS Technology"; 1993; pp. 86-88									
EO	AN	ù	E. H. Snow et al.; "Polarization Phenomena and Other Properties of Phosphosilicate Glass Films on Silicon"; Journal of the Electrochemical									
			Society, March 1966; pp. 263-269									
EXAMINER	W	m	io lati			DATE CONSIDER	ED 18/2	101				
			considered, whether ext communication to		is in conform	ance with MPEP 609	; Draw line through c	itation if not in	conformance	and not consid	lered.	

S:\mi22\1741\ID2.wpd A2706011350N